## Test 3

## Dec. 7, 2015 <br> Electronic Circuits 1 <br> Prof. Woo-Young Choi

## Prob. 1 (40)

Consider the CG amplifier configuration shown below. Assume the transistor is in saturation with transconductance $\mathrm{gm}_{\mathrm{m}}$ and its channel length modulation effect can be model with resistance ro.

(a)(10) Determine the input resistance of the circuit shown above.
(b)(10) Determine the voltage gain of the above CG amplifier.

Now consider a cascaded amplifier shown below. Assume all three transistors are in saturation with transconductance $\mathrm{gm}_{\mathrm{m} 1}, \mathrm{~g}_{\mathrm{m} 2}, \mathrm{~g}_{\mathrm{m}}$ and their channel length modulation effects can be model with resistance $\mathrm{r}_{01}, \mathrm{r}_{02}, \mathrm{r}_{03}$.

(c)(5) Give the amplifier configurations for $M_{1}$ and $M_{2}$, and identify the role of M3.
(d)(5) Determine the input resistance for $M_{2}$ when looked from its source terminal. You may use the result obtained in (a).
(e)(10) Determine the voltage gain of above cascaded amplifier. You may use the result obtained in (b). What does the voltage gain become if $g_{m 1}=g_{m 2}=g_{m 3}=g_{m}$, $r_{01}=r_{02}=r_{03}=r_{0}$ and $g_{m} r_{0} \gg 1$ ?

Prob. 2 (30)
Consider the $C S$ amplifier circuit shown below. $\mathrm{V}_{\mathrm{DD}}=1.5 \mathrm{~V}, \mathrm{~V}_{\mathrm{G}}=1.5 \mathrm{~V}, \mathrm{R}_{\mathrm{D}}=1 \mathrm{~K} \Omega$, $\mu_{\mathrm{n}} \mathrm{C}_{\mathrm{ox}}=200 \mu \mathrm{~A} / \mathrm{V}^{2}, \mathrm{~W} / \mathrm{L}=10, \mathrm{~V}_{\mathrm{TH}}=0.5 \mathrm{~V}$ and $\lambda=0$.

(a)(10) Determine the bias drain current in the above circuit. What mode of operation is $M_{1}$ in?
(b)(10) Draw the small-signal model of the above circuit when a small-signal input voltage is applied between $\mathrm{V}_{\mathrm{G}}$ and the gate of $\mathrm{M}_{1}$.
(c)(10) Determine the numerical value for the small-signal voltage gain.

## Prob. 3 (30)

We want to realize a current source having a desired current (Io) and a very large output resistance ( $R_{o u t}$ ) with the circuit shown below. Assume all MOS transistors are in saturation, and identical with $\frac{\mathrm{w}}{\mathrm{L}}=100, \mathrm{~V}_{\mathrm{th}}=0.7 \mathrm{~V}$, and $\mu_{\mathrm{n}} \mathrm{C}_{\mathrm{ox}}=200 \mu \mathrm{~A} / \mathrm{V}^{2}$.

(a)(10) Determine the numerical value for $R$ so that $I o=100 \mu \mathrm{~A}$. For this part, ignore the channel length modulation effect. (Hint: All transistors have the same drain current)
(b)(10) What is the smallest value for $V_{o}$ with which the above circuit can function as a current source? For this part, ignore the channel length modulation effect.
(c)(10) Determine the expression for output resistance, Rout. Consider the channel length modulation effect with ro. Your answer should be an expression of $g_{m}$ and $r_{0}$.

